

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1053	(257/411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB.	OR	OFF	2008/01/22 08:16
S1	2	"20050247985"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/07 17:53
S3	21739	high adj dielectric adj constant	US-PGPUB; USPAT	OR	ON	2007/05/08 14:59
S4	2218	gate and (gate near insulat\$3) and (Hfsi Zr)	US-PGPUB; USPAT	OR	ON	2007/06/02 17:24
S5	710	S3 and S4	US-PGPUB; USPAT	OR	ON	2007/05/08 15:07
S6	174665	gate and silicon oxide and depth and distribut\$3 and ((gate near insulat\$3) near (Zr Hf Ta Al Ti Nb Sc Y La Ce Pr Nd Sm Eu Gd Tb Dy Ho Er Tm Yb Lu))	US-PGPUB; USPAT	OR	ON	2007/05/08 15:07
S7	2075	S6 and S4	US-PGPUB; USPAT	OR	ON	2007/05/08 15:07
S8	204	S5 and @ad<"20020619"	US-PGPUB; USPAT	OR	ON	2007/05/08 15:08
S13	569	(tan hfo si) adj mosfet	US-PGPUB; USPAT	OR	ON	2007/06/02 17:38
S14	310	S13 and @ad<"20020627"	US-PGPUB; USPAT	OR	ON	2007/06/02 17:30
S15	0	(tan hfo) adj mosfet	US-PGPUB; USPAT	OR	ON	2007/06/02 17:38
S16	21	(tan hfo) near2 mosfet	US-PGPUB; USPAT	OR	ON	2007/06/02 17:42
S17	20	(hag-ju near cho).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 17:47
S18	14	("20020104481" "5316982" "5668021" "5668054" "6153519" "6168991" "6203613" "6204204" "6221712" "6357901" "6492217" "6504214" "6537901" "6607958").PN.	US-PGPUB; USPAT	OR	ON	2007/06/02 17:54
S19	7	"6380104"	US-PGPUB; USPAT	OR	ON	2007/06/02 23:10
S20	0	(Tanaka adj nobufumi).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 22:02
S21	0	(Tanaka near nobufumi).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 22:02

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S22	148	(nobufumi).in.	US-PGPUB; USPAT	OR	ON	2007/06/02 22:02
S23	637302	nitrogen	US-PGPUB; USPAT	OR	ON	2007/06/02 22:03
S24	17	S22 and S23	US-PGPUB; USPAT	OR	ON	2007/06/02 22:04
S25	0	(stack\$3 adj gate) with (nitrogen adj concentrat\$3) with (high adj dielectric adj constant) and (gate near insulat\$3) and (silicon adj oxide)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:06
S26	7	(stack\$3 adj gate) and (nitrogen adj concentrat\$3) and (high adj dielectric adj constant) and (gate near insulat\$3) and (silicon adj oxide)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:09
S27	16	(stack\$3 adj gate) and (nitrogen adj concentrat\$3) and (high adj dielectric adj constant)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:09
S28	38	(stack\$3 near gate) and (nitrogen adj concentrat\$3) and (high adj dielectric adj constant)	US-PGPUB; USPAT	OR	ON	2007/06/02 22:22
S29	40	"5891798"	US-PGPUB; USPAT	OR	ON	2007/06/02 22:22
S30	158	Dharmarajan.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/02 22:59
S31	6	"6365467"	US-PGPUB; USPAT	OR	ON	2007/06/02 23:10
S32	8784	((438/197) or (438/299) or (438/585) or (438/587) or (438/588) or (438/592) or (438/652) or (438/653) or (438/654) or (438/656) or (438/657) or (438/680) or (438/684)).CCLS.	US-PGPUB; USPAT	OR	OFF	2007/06/11 10:47
S33	0	high near dielectric near3 gate near instulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:31
S34	0	high near dielectric and gate near instulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:41

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S35	5868	(high near dielectric) and (gate near insulat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:41
S36	950	stack\$3 near gate near electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:47
S37	47	S35 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 16:47